Attorney Docket No.: YOR920020287US1

Date: January 21, 2004

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Patents, P_AO. Box 1450, Alexandria, VA 22313-1450



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Patent Application

Applicant(s): Allen et al.

Docket No.:

YOR920030175US1

Serial No.:

10/661,041

Filed:

September 12, 2003

Group:

2811

Examiner:

Unassigned

Title:

Techniques for Patterning Features in Semiconductor Devices

INFORMATION DISCLOSURE STATEMENT

Commissioner of Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Pursuant to 37 C.F.R. §§1.56, 1.97 and 1.98, Applicants' attorney wishes to bring to the attention of the Patent and Trademark Office the following documents listed on the accompanying PTO Form 1449.

U.S. Patent

1. U.S. Patent No. 6,316,167

Copies of each of the following listed items are enclosed:

Other Documents

- 2. Chun et al., "Contact Hole Size Reducing Methods by Using Water-Soluble Organic Over-Coating Material (WASOOM) as a Barrier Layer Toward 0.15 um Contact Hole; Resist Flow Technique I," Proc. SPIE, Vol. 3999, pgs. 620-626 (2000).
- 3. Chung et al., "A Novel Resist Material for sub-100 nm Contact Hole Pattern," Proc. SPIE, Vol. 3999, pgs. 305-312 (2000).
- DellaGuardia et al., "193 Lithography and RELACS™ Processing for BEOL Lithography," Proc. SPIE, Vol. 4346, pgs. 1029-1040 (2001).
 Lucas et al., "193 nm Contact Photoresist Reflow Feasibility Study," Proc.
- 5. Lucas et al., "193 nm Contact Photoresist Reflow Feasibility Study," Proc. SPIE, Vol. 4345, pgs. 725-736 (2001).
- 6. Satou et al., "Sub-0.10 μm Hole Fabrication Using Bilayer Silylation Process for 193 nm Lithography," Jpn. J. Appl. Phys. 1, Vol. 38, Part 1, No. 12B, pgs 7008-7012 (December 1999).

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In the event of non-payment or improper payment of a required fee, the Commissioner is authorized to charge or the credit **International Business Machines Corporation's Deposit Account**No. 50-0510 as required to correct the error.

The filing of this Information Disclosure Statement shall not be construed as a representation that a search has been made, or as an admission that the information cited is considered to be material to patentability or as a representation that no other material information exists.

Respectfully submitted,

Date: January 21, 2004

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FORM PTO-1449 (MODIFIED)

LIST OF PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT

Applicant(s): Allen et al. Docket No.: YOR92003

YOR920030175US1

Serial No.: Filing Date:

10/661,041 September 12, 2003

Group:

2811



U.S. PATENT DOCUMENTS					
EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS/SUBCLASS	FILING DATE IF APPROPRIATE
	6,316,167	11/13/01	Angelopoulos et al.	430/313	
FOREIGN PATENT DOCUMENTS					
EXAMINER				OL ASSIGNABILITY ASS	TRANSLATION
INITIAL	DOCUMENT NO.	DATE	COUNTRY	CLASS/SUBCLASS	YES NO
					
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EXAMINER			OTHER DOCUMENTS		
INITIAL	REF NO. AU	THOR, TITLE, DATE, PE	ERTINENT PAGES, ETC.		
	Chun et al., "Contact Hole Size Reducing Methods by Using Water-Soluble Organic Over-Coating Material (WASOOM) as a Barrier Layer Toward 0.15 um Contact Hole; Resist Flow Technique I," Proc. SPIE, Vol. 3999, pgs. 620-626 (2000).				
	Chung et al., "A Novel Resist Material for sub-100 nm Contact Hole Pattern," Proc. SPIE, Vol. 3999, pgs. 305-312 (2000).				
	DellaGuardia et al., "193 Lithography and RELACS™ Processing for BEOL Lithography," Proc. SPIE, Vol. 4346, pgs. 1029-1040 (2001).				
	Lucas et al., "193 nm Contact Photoresist Reflow Feasibility Study," Proc. SPIE, Vol. 4345, pgs. 725-736 (2001).				
	Satou et al., "Sub-0.10 µm Hole Fabrication Using Bilayer Silylation Process for 193 nm Lithography," Jpn. J. Appl. Phys. 1, Vol. 38, Part 1, No. 12B, pgs 7008-7012 (December 1999).				
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Examiner			-	Date Considere	ed

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.